Physics FSC Part 2 Chapter 18 Online MCQ's Test

Sr	Questions	Answers Choice
1	A transistor has parts:	A. 2 B. 3 C. 4 D. 5
2	The circuit of full wave rectification consist of	A. Three diodes B. Four diodes C. Two diodes D. One diode
3	When a PN-Junction is reverse biased the depletion region is.	A. Widened B. Narrowed C. Normal D. None of these
4	In a transistor, collector current is controlled by:	A. Collector voltage B. Base current C. Collector resistance D. All of the above
5	The output voltage of a rectifier is.	A. Smooth B. Pulsating C. Alternating D. Per featly direct
6	Photo diode detects.	A. Visible light B. Radio waves C. X rays D. All of them
7	Most of the electrons in the base of an NPN transistor flow:	A. Out of the base lead B. Into the collector C. Into the emit D. Into the base supply
8	The potential barrier for silicon is.	A. 0.7 V B. 0.5 V C. 0.3 V D. 0.9 V
9	Doping is made comparatively larger in	A. Emitter B. Base C. Collector D. P -type semi conductor
10	For normal transistor the emitter current can be given by	A. I_E = I_C B. I_E = I_C + I_B C. I_E = I_B D. None of these
11	NAND gate represented by:	A. X = A. B B. X = A+B C. X= A.B D. X=|A+B|
12	The ratio Beta in transistor is called.	A. Voltage gain B. Emitter gain C. Current gain D. Nuclear gain
13	Pulsating output of full wave rectifier can be made smooth by using circuit called.	A. Filter B. Amplifier C. Resistor D. Transistor
14	The potential difference across depletion region in case of Si is	A. 0.6 volt B. 0.9 volt C. 0.7 volt D. 0.2 volt
15	A device which converts low voltage or current to high voltage or current is called.	A. Transformer B. AC generator C. Amplifier D. Rectifier

		D. Rectifier
16	The output of two input is zero only when its.	A. Both inputs are zero B. Either input is zero C. Both inputs are one D. Either input is one
17	The potential difference across the depletion region of germanium is.	A. 0.3 V B. 0.5 V C. 0.7 V D. 0.8 V
18	The chargeless region after formation of Pn junction is called:	A. Free region B. Depletion region C. Field region D. U.V region
19	The term invertor is used for.	A. NOR gate B. XNOR gate C. NAND gate D. NOT gate
20	The ratio of potential barriers of Ge to Si at room temperatrue is.	A. 7:3 B. 1:3 C. 2:5 D. 3:7